

**Remarks**

Reconsideration and reversal of the rejections expressed in the Office Action of May 31, 2005 are respectfully contended in view of the following remarks and the application as amended. The present invention relates to a method for removing etching assist gas from a fabrication system used during defect repair of a photomask in the fabrication of an integrated circuit, comprising: (a) inspecting the photomask and detecting a defect, said defect in a defect region; and (b) repairing said defect, wherein an amount, effective for the purpose of styrene is added to the system. By the method of the present invention, the amount of gas remaining on the Mosi film is reduced, resulting in less surface damage present on the photomask.

The objection to the specification has been overcome by the clarification made to paragraph 12, as noted above.

Claims 1, 6 and 11 were rejected under 35 U.S.C. §112, second paragraph. The claims have been clarified as suggested by the Examiner at page 2 of the Office Action. Support for such clarifications are found at, e.g., paragraph 9 of the specification as filed. Therefore, this rejection is overcome.

For all of the above reasons, it is respectfully contended that the solicited claims define patentable subject matter. Reconsideration and reversal of the rejections expressed in the Office Action of May 31, 2005 are respectfully submitted. The Examiner is invited to call the undersigned if any questions arise during the course of reconsideration of this matter.

Respectfully submitted,

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